

FIG. 2

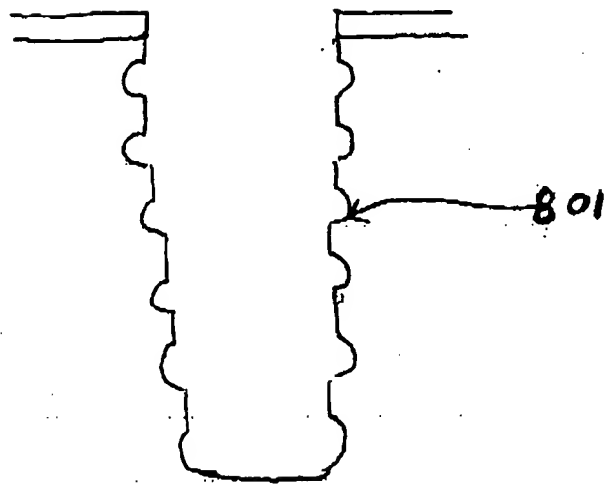


FIG. 8

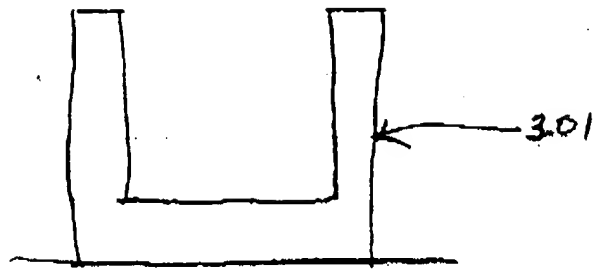


FIG. 3

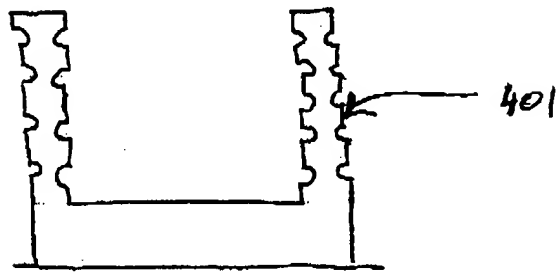


FIG. 4



FIG. 5

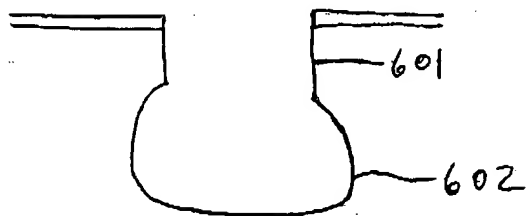


FIG. 6

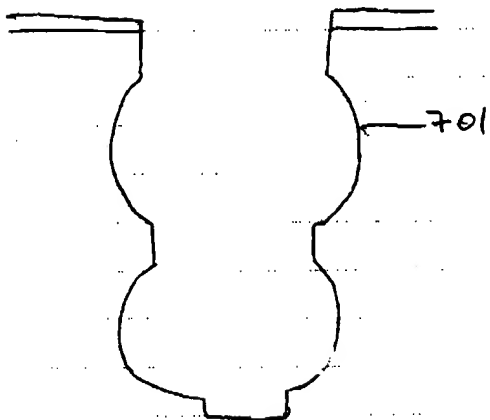


FIG. 7

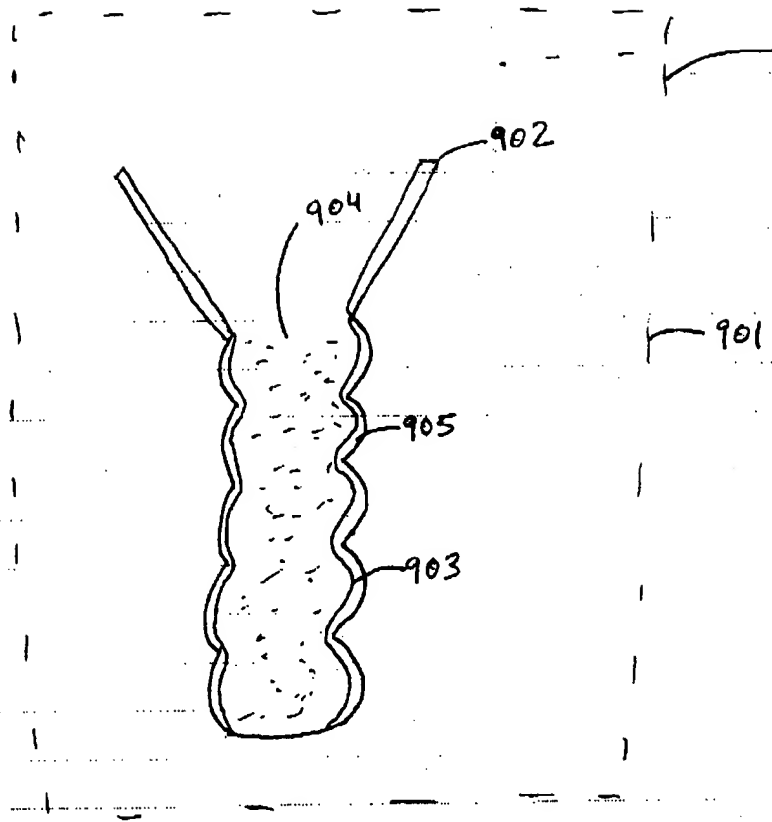


FIG. 9



FIG. 10

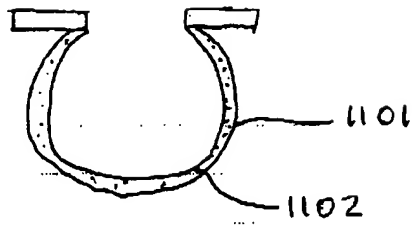


FIG. 11

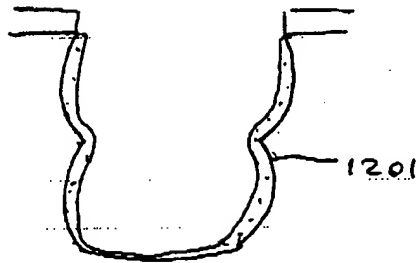


FIG. 12

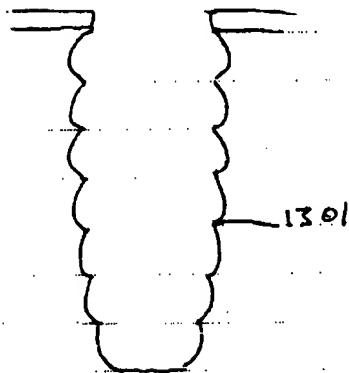


FIG. 13

FOOTPRINT 00025660

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graph TD; Start([START]) --> 1401[LOAD SILICON SUBSTRATE INTO PLASMA ETCH CHAMBER]; 1401 --> 1402[PERFORM ISOTROPIC ETCH ON SUBSTRATE]; 1402 --> 1403[PERFORM ANISOTROPIC ETCH ON SUBSTRATE]; 1403 --> 1404{HAS SUFFICIENT DRAIN BEEN ACHIEVED?}; 1404 -- No --> 1402; 1404 -- Yes --> 1405[REMOVE SUBSTRATE FROM CHAMBER]; 1405 --> Stop([STOP]);
```

Flowchart 1400 illustrates a method for etching a substrate. The process begins with a START terminal, leading to step 1401: LOAD SILICON SUBSTRATE INTO PLASMA ETCH CHAMBER. This is followed by step 1402: PERFORM ISOTROPIC ETCH ON SUBSTRATE, and then step 1403: PERFORM ANISOTROPIC ETCH ON SUBSTRATE. A decision diamond 1404 asks: HAS SUFFICIENT DRAIN BEEN ACHIEVED? If the answer is No, the process loops back to step 1402. If the answer is Yes, the process proceeds to step 1405: REMOVE SUBSTRATE FROM CHAMBER, and finally to a STOP terminal.

FIG 14

TOP SECRET - 00025660

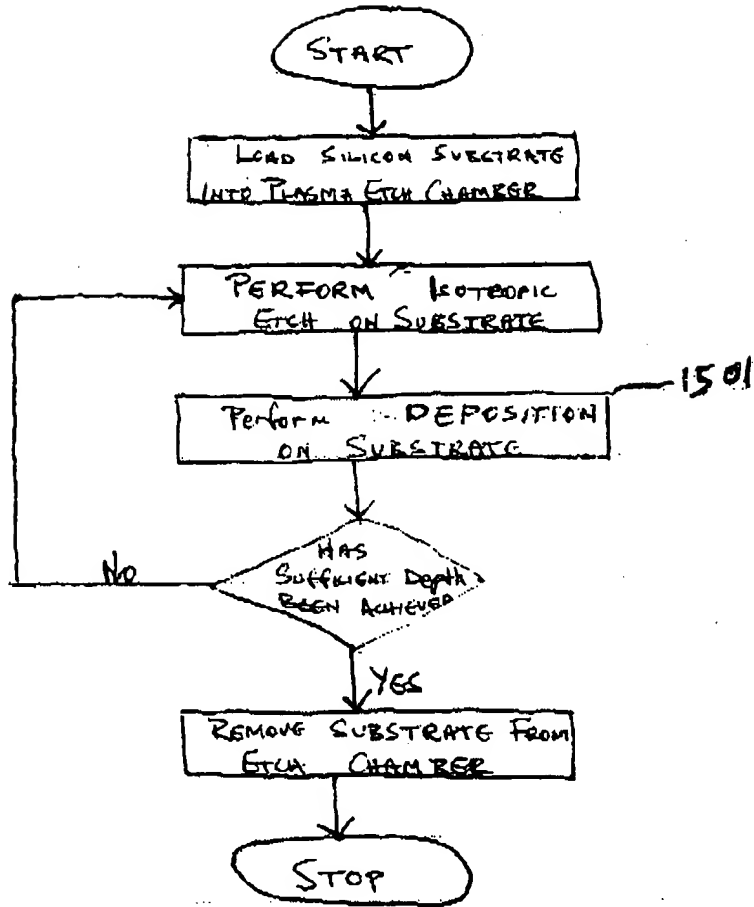


FIG. 15